

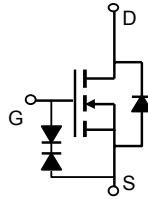
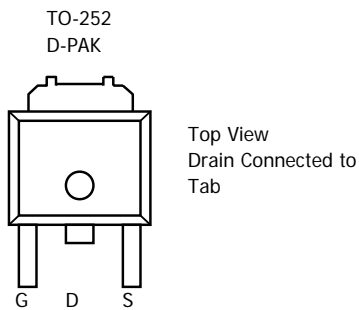
AOD434
N-Channel Enhancement Mode Field Effect Transistor

General Description

The AOD434 uses advanced trench technology to provide excellent $R_{DS(ON)}$, low gate charge and operation with gate voltages as low as 1.8V while retaining a 12V $V_{GS(MAX)}$ rating. It is ESD protected to a 2KV HBM rating. *Standard Product AOD434 is Pb-free (meets ROHS & Sony 259 specifications). AOD434L is a Green Product ordering option. AOD434 and AOD434L are electrically identical.*

Features

V_{DS} (V) = 20V
 I_D = 18A (V_{GS} = 10V)
 $R_{DS(ON)} < 14m\Omega$ (V_{GS} = 10V)
 $R_{DS(ON)} < 16m\Omega$ (V_{GS} = 4.5V)
 $R_{DS(ON)} < 21m\Omega$ (V_{GS} = 2.5V)
 $R_{DS(ON)} < 30m\Omega$ (V_{GS} = 1.8V)
 ESD Rating: 2KV HBM


Absolute Maximum Ratings $T_A=25^\circ\text{C}$ unless otherwise noted

Parameter	Symbol	Maximum	Units
Drain-Source Voltage	V_{DS}	20	V
Gate-Source Voltage	V_{GS}	± 12	V
Continuous Drain Current ^G	I_D	$T_C=25^\circ\text{C}$	A
		$T_C=100^\circ\text{C}$	
Pulsed Drain Current ^C	I_{DM}	30	
Avalanche Current ^C	I_{AR}	18	A
Repetitive avalanche energy $L=0.1\text{mH}$ ^C	E_{AR}	37	mJ
Power Dissipation ^B	P_D	$T_C=25^\circ\text{C}$	W
		$T_C=100^\circ\text{C}$	
Power Dissipation ^A	P_{DSM}	$T_A=25^\circ\text{C}$	W
		$T_A=70^\circ\text{C}$	
Junction and Storage Temperature Range	T_J, T_{STG}	-55 to 175	$^\circ\text{C}$

Thermal Characteristics

Parameter	Symbol	Typ	Max	Units
Maximum Junction-to-Ambient ^A	$R_{\theta JA}$	16.7	25	$^\circ\text{C/W}$
Maximum Junction-to-Ambient ^A		Steady-State	40	50
Maximum Junction-to-Case ^B	$R_{\theta JC}$	1.9	2.5	$^\circ\text{C/W}$

Electrical Characteristics ($T_J=25^\circ\text{C}$ unless otherwise noted)

Symbol	Parameter	Conditions	Min	Typ	Max	Units
STATIC PARAMETERS						
BV_{DSS}	Drain-Source Breakdown Voltage	$I_D=250\mu\text{A}$, $V_{GS}=0\text{V}$	20			V
I_{DSS}	Zero Gate Voltage Drain Current	$V_{DS}=16\text{V}$, $V_{GS}=0\text{V}$ $T_J=55^\circ\text{C}$			1	μA
					5	
I_{GSS}	Gate-Body leakage current	$V_{DS}=0\text{V}$, $V_{GS}=\pm 10\text{V}$			10	μA
BV_{GSO}	Gate-Source Breakdown Voltage	$V_{DS}=0\text{V}$, $I_G=\pm 250\mu\text{A}$	± 12			V
$V_{GS(th)}$	Gate Threshold Voltage	$V_{DS}=V_{GS}$, $I_D=250\mu\text{A}$	0.5	0.75	1	V
$I_{D(ON)}$	On state drain current	$V_{GS}=4.5\text{V}$, $V_{DS}=5\text{V}$	30			A
$R_{DS(ON)}$	Static Drain-Source On-Resistance	$V_{GS}=10\text{V}$, $I_D=18\text{A}$ $T_J=125^\circ\text{C}$		10.9	14	m Ω
				14.3	18	
		$V_{GS}=4.5\text{V}$, $I_D=15\text{A}$		12.6	16	m Ω
		$V_{GS}=2.5\text{V}$, $I_D=10\text{A}$		16.5	21	m Ω
	$V_{GS}=1.8\text{V}$, $I_D=5\text{A}$		23.2	30	m Ω	
g_{FS}	Forward Transconductance	$V_{DS}=5\text{V}$, $I_D=18\text{A}$		36		S
V_{SD}	Diode Forward Voltage	$I_S=1\text{A}$, $V_{GS}=0\text{V}$		0.73	1	V
I_S	Maximum Body-Diode Continuous Current				18	A
DYNAMIC PARAMETERS						
C_{iss}	Input Capacitance	$V_{GS}=0\text{V}$, $V_{DS}=10\text{V}$, $f=1\text{MHz}$		1810		pF
C_{oss}	Output Capacitance			232		pF
C_{rss}	Reverse Transfer Capacitance			200		pF
R_g	Gate resistance	$V_{GS}=0\text{V}$, $V_{DS}=0\text{V}$, $f=1\text{MHz}$		1.6		Ω
SWITCHING PARAMETERS						
$Q_g(10\text{V})$	Total Gate Charge	$V_{GS}=10\text{V}$, $V_{DS}=10\text{V}$, $I_D=18\text{A}$		40.1		nC
$Q_g(4.5\text{V})$	Total Gate Charge			8.9		
Q_{gs}	Gate Source Charge			1.7		nC
Q_{gd}	Gate Drain Charge			6.2		nC
$t_{D(on)}$	Turn-On Delay Time	$V_{GS}=10\text{V}$, $V_{DS}=10\text{V}$, $R_L=0.56\Omega$, $R_{GEN}=3\Omega$		4		ns
t_r	Turn-On Rise Time			15		ns
$t_{D(off)}$	Turn-Off Delay Time			42.2		ns
t_f	Turn-Off Fall Time			18.2		ns
t_{rr}	Body Diode Reverse Recovery Time	$I_F=18\text{A}$, $dI/dt=100\text{A}/\mu\text{s}$		23.2		ns
Q_{rr}	Body Diode Reverse Recovery Charge	$I_F=18\text{A}$, $dI/dt=100\text{A}/\mu\text{s}$		4.9		nC

A: The value of $R_{\theta JA}$ is measured with the device mounted on 1in² FR-4 board with 2oz. Copper, in a still air environment with $T_A=25^\circ\text{C}$. The Power dissipation P_{DSM} is based on $R_{\theta JA}$ and the maximum allowed junction temperature of 150°C . The value in any given application depends on the user's specific board design, and the maximum temperature of 175°C may be used if the PCB allows it.

B: The power dissipation P_D is based on $T_{J(MAX)}=175^\circ\text{C}$, using junction-to-case thermal resistance, and is more useful in setting the upper dissipation limit for cases where additional heatsinking is used.

C: Repetitive rating, pulse width limited by junction temperature $T_{J(MAX)}=175^\circ\text{C}$.

D: The $R_{\theta JA}$ is the sum of the thermal impedance from junction to case $R_{\theta JC}$ and case to ambient.

E: The static characteristics in Figures 1 to 6 are obtained using $<300\mu\text{s}$ pulses, duty cycle 0.5% max.

F: These tests are performed with the device mounted on 1 in² FR-4 board with 2oz. Copper, in a still air environment with $T_A=25^\circ\text{C}$. The SOA curve provides a single pulse rating.

G: The maximum current rating is limited by bond-wires.

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TYPICAL ELECTRICAL AND THERMAL CHARACTERISTICS

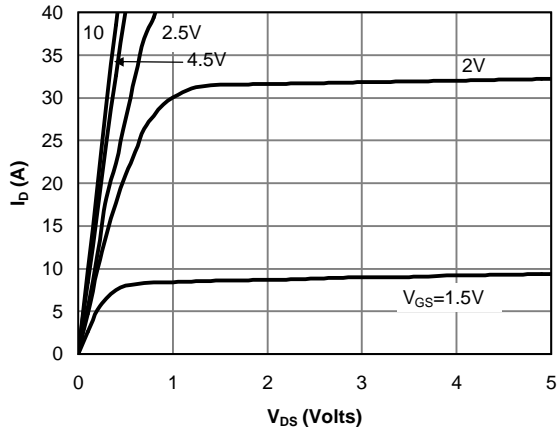


Fig 1: On-Region Characteristics

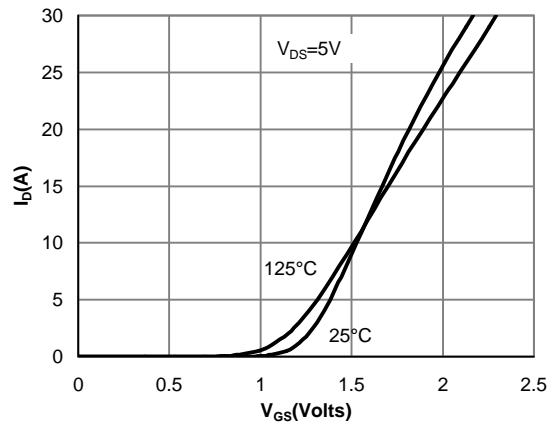


Figure 2: Transfer Characteristics

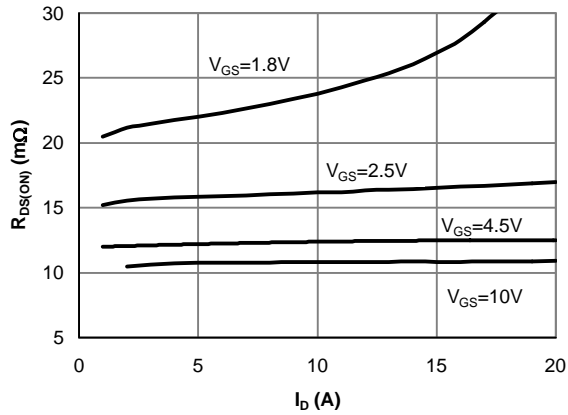


Figure 3: On-Resistance vs. Drain Current and Gate Voltage

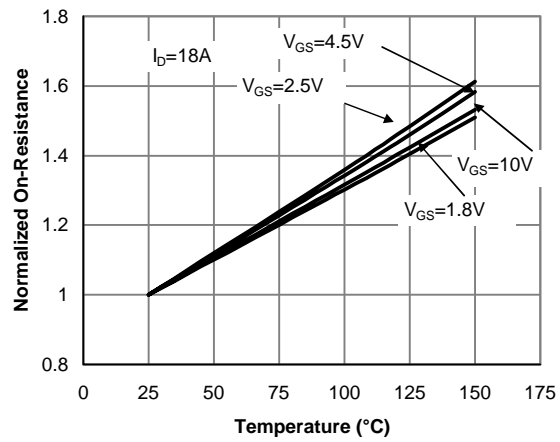


Figure 4: On-Resistance vs. Junction Temperature

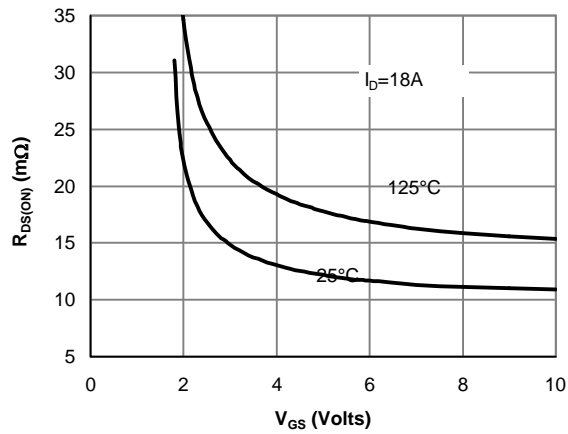


Figure 5: On-Resistance vs. Gate-Source Voltage

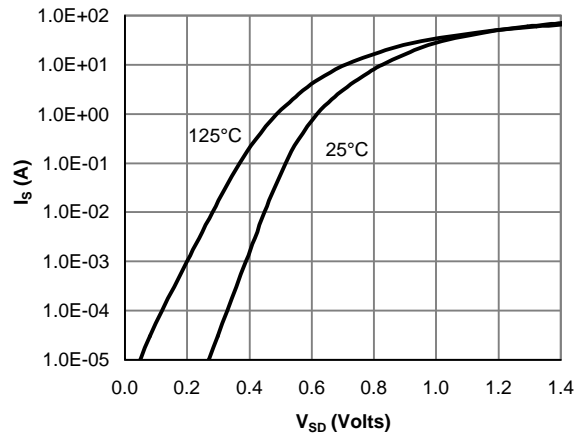


Figure 6: Body-Diode Characteristics

TYPICAL ELECTRICAL AND THERMAL CHARACTERISTICS

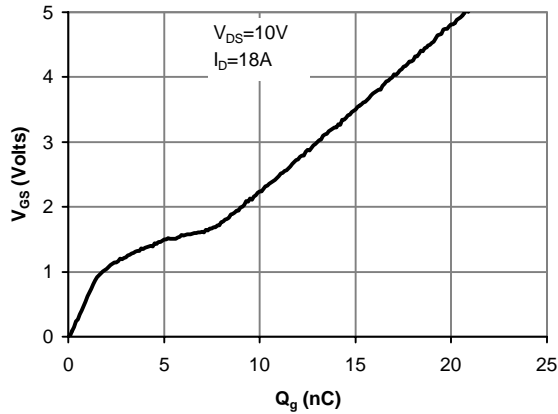


Figure 7: Gate-Charge Characteristics

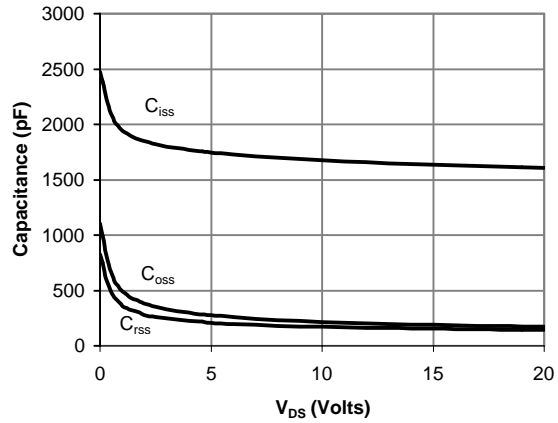


Figure 8: Capacitance Characteristics

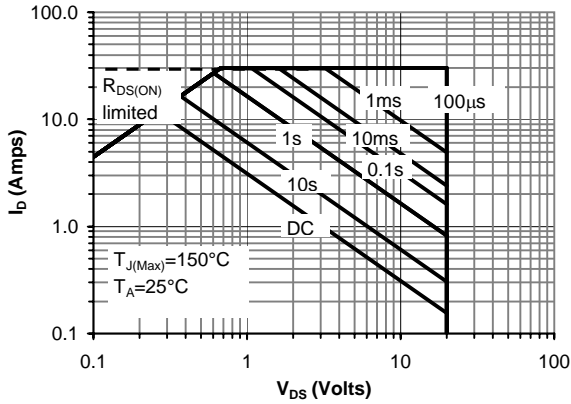


Figure 9: Maximum Forward Biased Safe Operating Area (Note E)

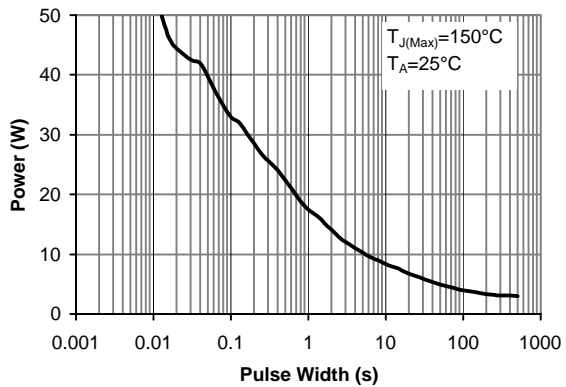


Figure 10: Single Pulse Power Rating Junction-to-Ambient (Note E)

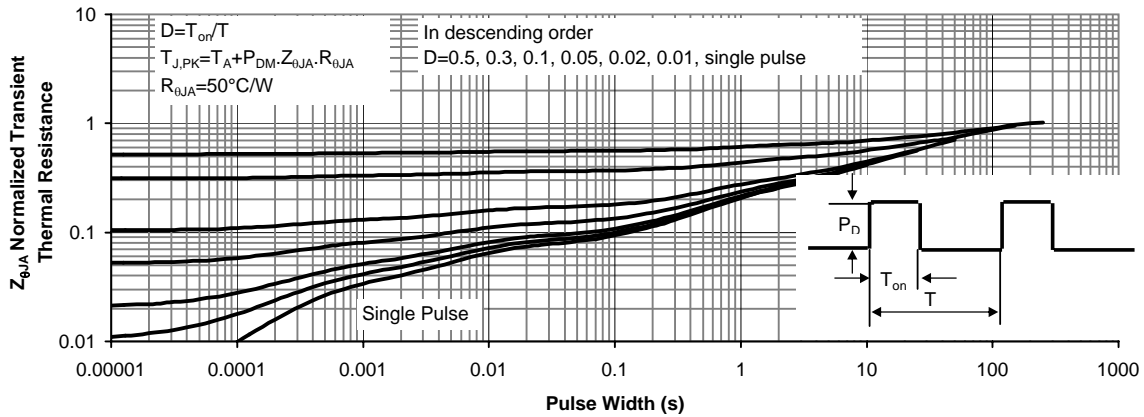


Figure 11: Normalized Maximum Transient Thermal Impedance